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SEMICONDUCTOR

November 2013

FQD13N06 N-Channel QFET® MOSFET

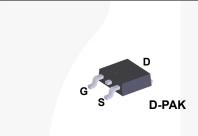
60 V, 10 A, 140 mΩ

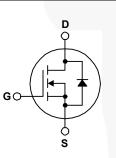
Description

This N-Channel enhancement mode power MOSFET is • 10 A, 60 V, $R_{DS(on)}$ = 140 m Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state $I_D = 5.0 \text{ A}$ Low Gate Charge (Typ. 5.8 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 15 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_{D} = 5.0 \text{ A}$





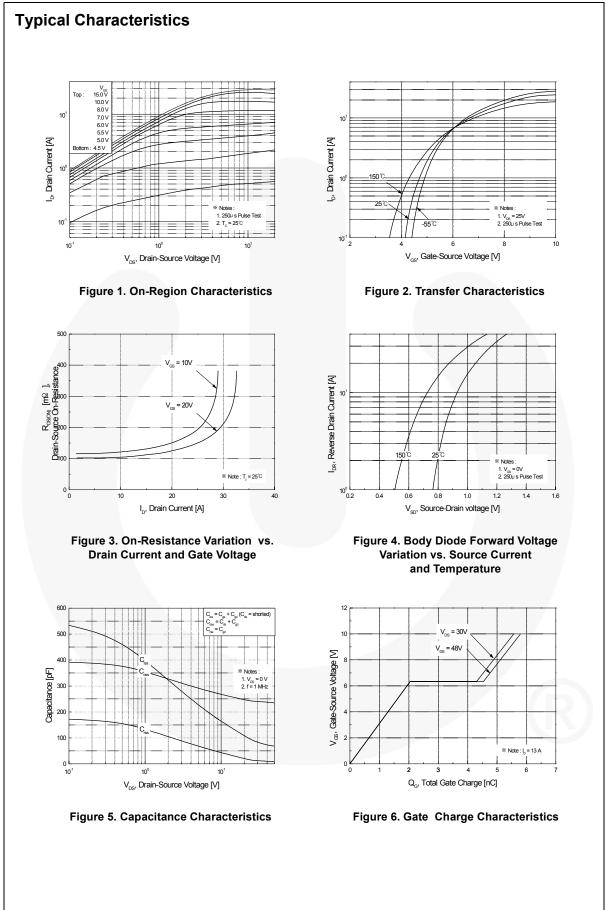
Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

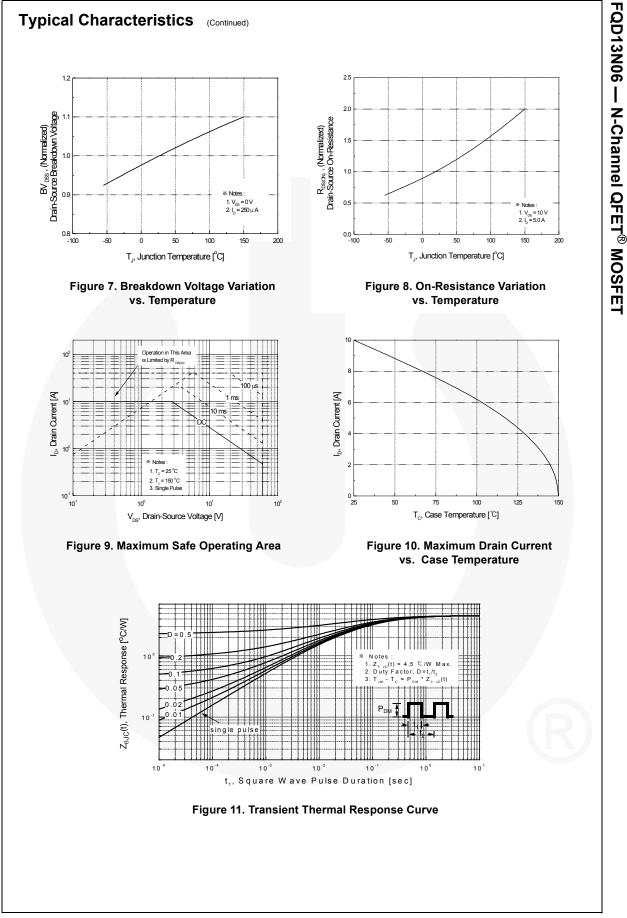
Symbol	Parameter		FQD13N06TM	Unit
V _{DSS}	Drain-Source Voltage		60	V
I _D	Drain Current - Continuous (T _C = 25°C)		10	A
	- Continuous (T _C = 100°C)		6.3	A
I _{DM}	Drain Current - Pulsed	(Note 1)	40	A
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		85	mJ
I _{AR}	Avalanche Current (Note 1)		10	A
E _{AR}	Repetitive Avalanche Energy (Note 1)		2.8	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
P_D Power Dissipation ($T_A = 25^{\circ}C$) *			2.5	W
	Power Dissipation ($T_C = 25^{\circ}C$)		28	W
	- Derate above 25°C		0.22	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
TI	Maximum lead temperature for soldering,		300	°C
'L	1/8" from case for 5 seconds		300	C

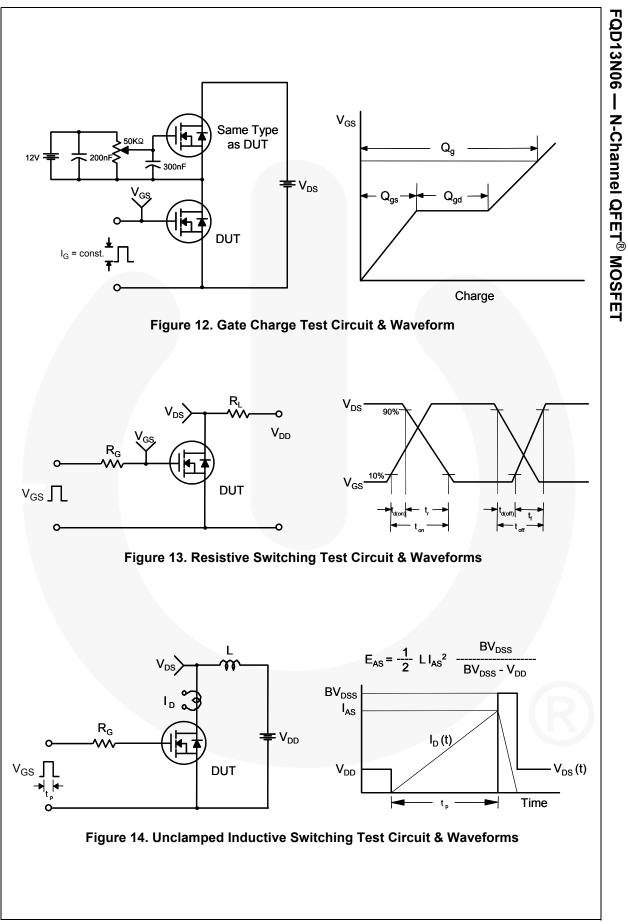
Thermal Characteristics

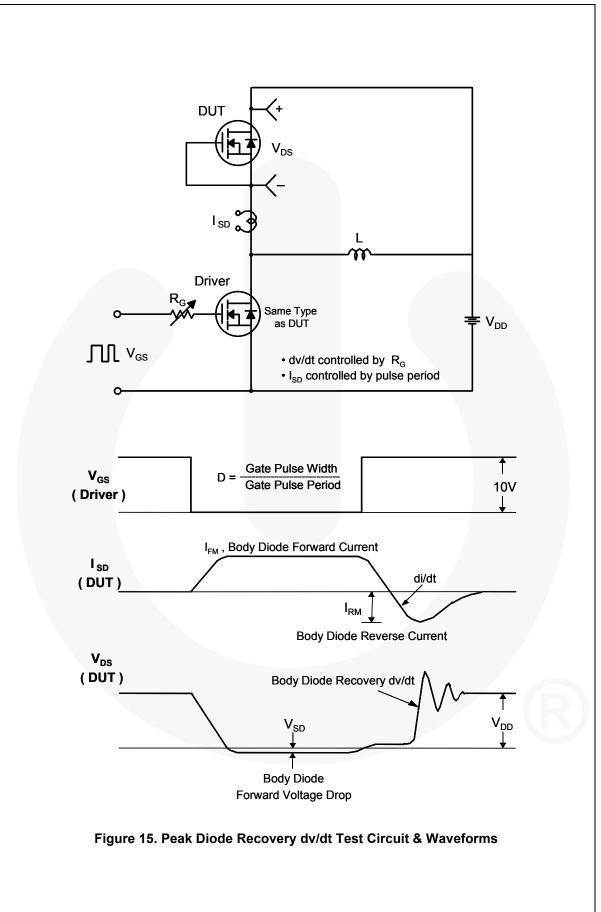
Symbol	Parameter	FQD13N06TM	Unit
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	4.5	
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

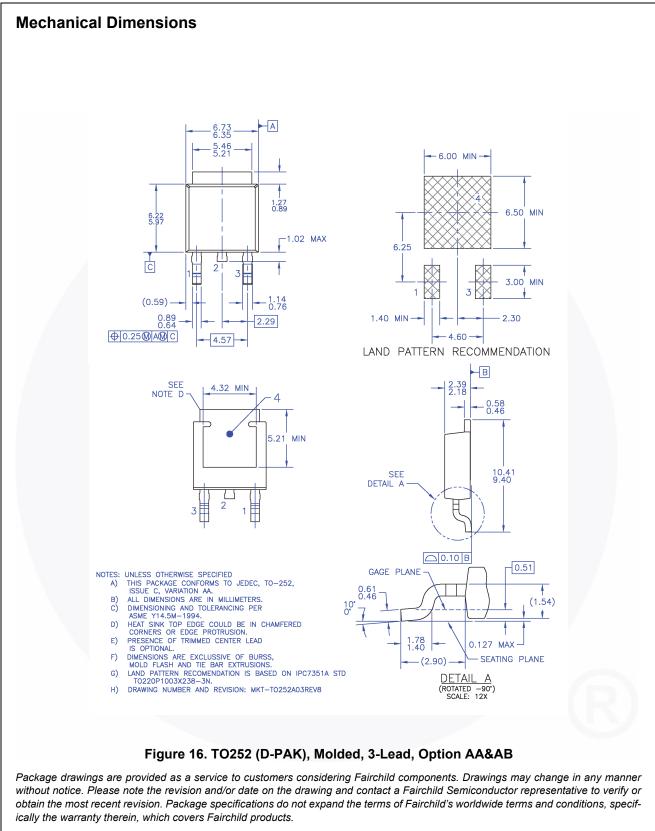
•		Packag	je Pacl	king Methoo	d Ree	l Size	Tape V	Vidth	Quantity
		DPAK	PAK Tape and Reel 330) mm	16 mm		2500 units	
cal Cha	racteristics	T _C = 25°C un	less otherwise no	oted.					
	Parameter		Test C	onditions		Min.	Тур.	Max.	Unit
racterist	ics								
		e V	′ _{GS} = 0 V, I _D =	= 250 μA		60			V
	•	_	$I_D = 250 \ \mu$ A, Referenced to 25° C				0.06		V/°C
Zoro Coto	Voltago Drain Current	V	′ _{DS} = 60 V, V ₀	_{GS} = 0 V				1	μA
Zero Gale	vollage Drain Current	V	′ _{DS} = 48 V, T ₍	_c = 125°C				10	μA
Gate-Body	/ Leakage Current, For		ard $V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA	
Gate-Body	/ Leakage Current, Rev	verse V	′ _{GS} = -25 V, V	′ _{DS} = 0 V				-100	nA
racterist	ics								
Gate Thre	shold Voltage	V	ν _{DS} = V _{GS} , I _D	= 250 μA		2.0		4.0	V
Static Dra	n-Source On-Resistan	ce V	′ _{GS} = 10 V, I _D	= 5.0 A			0.11	0.14	Ω
Forward T	ransconductance	V	′ _{DS} = 25 V, I _D	= 5.0 A		-	4.9		S
ic Charad	teristics								
i									
Input Cap	acitance	V	= 25 V V	= 0 V			240	310	pF
Output Cap			′ _{DS} = 25 V, V ₀ = 1 0 MHz	_{GS} = 0 V,			240 90	310 120	pF pF
Output Ca			′ _{DS} = 25 V, V ₀ = 1.0 MHz	_{GS} = 0 V,					
Output Ca Reverse T	pacitance ransfer Capacitance			_{3S} = 0 V,			90	120	pF
Output Ca Reverse T ng Chara	pacitance ransfer Capacitance acteristics	f	= 1.0 MHz				90	120	pF
Output Ca Reverse T	pacitance ransfer Capacitance acteristics Delay Time	f	= 1.0 MHz / _{DD} = 30 V, I _D				90 15	120 20	pF pF
Output Ca Reverse T ng Chara Turn-On D	pacitance iransfer Capacitance acteristics belay Time tise Time	f	= 1.0 MHz				90 15 5	120 20 20	pF pF ns
Output Ca Reverse T ng Chara Turn-On E Turn-On F	pacitance iransfer Capacitance acteristics Delay Time tise Time Delay Time	f	= 1.0 MHz / _{DD} = 30 V, I _D	= 6.5 A,	(Note 4)	 	90 15 5 25	120 20 20 60	pF pF ns ns
Output Ca Reverse T ng Chara Turn-On E Turn-On F Turn-Off E	pacitance iransfer Capacitance acteristics belay Time tise Time belay Time all Time	f	= 1.0 MHz / _{DD} = 30 V, I _D g _G = 25 Ω	= 6.5 A,	(Note 4)	 	90 15 5 25 8	120 20 20 60 25	pF pF ns ns ns
Output Ca Reverse T ng Chara Turn-On E Turn-Off E Turn-Off F Total Gate	pacitance iransfer Capacitance acteristics belay Time tise Time belay Time all Time	f	= 1.0 MHz / _{DD} = 30 V, I _D	= 6.5 A,	(Note 4)	 	90 15 5 25 8 15	120 20 20 60 25 40	pF pF ns ns ns ns ns
Output Ca Reverse T ng Chara Turn-On E Turn-Off E Turn-Off F Total Gate	pacitance iransfer Capacitance acteristics belay Time tise Time belay Time all Time charge cce Charge	f	= 1.0 MHz $f_{DD} = 30 \text{ V}, \text{ I}_{D}$ $g_{G} = 25 \Omega$ $f_{DS} = 48 \text{ V}, \text{ I}_{D}$	= 6.5 A, = 13 A,	(Note 4)	 	90 15 5 25 8 15 5.8	120 20 20 60 25 40 7.5	PF pF ns ns ns ns nc
Output Ca Reverse T ng Chara Turn-On E Turn-Off E Turn-Off F Total Gate Gate-Sour Gate-Drain	pacitance iransfer Capacitance acteristics belay Time tise Time elay Time all Time Charge ce Charge n Charge	f	= 1.0 MHz $V_{DD} = 30 \text{ V}, \text{ I}_{D}$ $R_{G} = 25 \Omega$ $V_{DS} = 48 \text{ V}, \text{ I}_{D}$ $V_{GS} = 10 \text{ V}$	= 6.5 A, = 13 A,	<u> </u>	 	90 15 5 25 8 15 5.8 2.0	120 20 20 60 25 40 7.5 	pF pF ns ns ns ns nc nC
Output Ca Reverse T ng Chara Turn-On E Turn-Off E Turn-Off F Total Gate Gate-Soun Gate-Drain	pacitance iransfer Capacitance acteristics belay Time tise Time all Time charge ce Charge n Charge ode Characteristi	f	= 1.0 MHz $T_{DD} = 30 V, I_D$ $R_G = 25 \Omega$ $T_{DS} = 48 V, I_D$ $T_{GS} = 10 V$ Maximum	= 6.5 A, = 13 A,	<u> </u>	 	90 15 5 25 8 15 5.8 2.0 2.5	120 20 60 25 40 7.5 	pF pF ns ns ns nC nC nC
Output Ca Reverse T ng Chara Turn-On E Turn-Off E Turn-Off F Total Gate Gate-Sour Gate-Drain Ource Di Maximum	pacitance iransfer Capacitance acteristics belay Time tise Time belay Time all Time Charge ree Charge n Charge ode Characteristi Continuous Drain-Sour	f V R V V V V V V V V V V	= 1.0 MHz $I_{DD} = 30 V, I_D$ $I_G = 25 Ω$ $I_{DS} = 48 V, I_D$ $I_{GS} = 10 V$ Maximum Forward Cur	= 6.5 A, = 13 A,	<u> </u>	 	90 15 5 25 8 15 5.8 2.0	120 20 20 60 25 40 7.5 10	PF pF ns ns ns nc nC nC nC
Output Ca Reverse T ng Chara Turn-On E Turn-Off E Turn-Off F Total Gate Gate-Sour Gate-Drain Cource Di Maximum Maximum	pacitance ransfer Capacitance acteristics belay Time tise Time elay Time all Time Charge ce Charge n Charge ode Characteristi Continuous Drain-Sour Pulsed Drain-Source D	f V R V V V V V V V V V V V V V V V V	= 1.0 MHz I_{DD} = 30 V, I_{D} I_{G} = 25 Ω I_{DS} = 48 V, I_{D} I_{GS} = 10 V Maximum Forward Current	= 6.5 A, = 13 A, • Ratings rent	<u> </u>	 	90 15 5 25 8 15 5.8 2.0 2.5	120 20 60 25 40 7.5 10 40	PF pF ns ns ns nc nC nC
Output Ca Reverse T ng Chara Turn-On E Turn-Off E Turn-Off F Total Gate Gate-Sour Gate-Drain Cource Di Maximum Maximum Drain-Sou	pacitance iransfer Capacitance acteristics belay Time tise Time belay Time all Time Charge ree Charge n Charge ode Characteristi Continuous Drain-Sour	f V R V V V V V V V V V V V V V V V V V	= 1.0 MHz $I_{DD} = 30 V, I_D$ $I_G = 25 Ω$ $I_{DS} = 48 V, I_D$ $I_{GS} = 10 V$ Maximum Forward Cur	= 6.5 A, = 13 A, = Ratings rent = 10 A	<u> </u>	 	90 15 25 8 15 5.8 2.0 2.5 	120 20 20 60 25 40 7.5 10	PF pF ns ns ns ns nC nC nC A A
	racterist Drain-Sou Breakdow Coefficien Zero Gate Gate-Body Gate-Body racterist Gate Thre Static Drai Forward T	Parameter racteristics Drain-Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, For Gate-Body Leakage Current, Rei racteristics Gate Threshold Voltage Static Drain-Source On-Resistan Forward Transconductance ic Characteristics	Parameter Imacteristics Drain-Source Breakdown Voltage V Breakdown Voltage Temperature Indext Coefficient Zero Gate Voltage Drain Current V Gate-Body Leakage Current, Forward V Gate-Body Leakage Current, Reverse V Imacteristics Gate Threshold Voltage V Static Drain-Source On-Resistance V Forward Transconductance V	ParameterTest CpracteristicsDrain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}, \text{ Ip} = 0 \text{ Breakdown Voltage Temperature CoefficientBreakdown Voltage Temperature CoefficientI_D = 250 \ \mu A, R = 25^{\circ}CZero Gate Voltage Drain CurrentV_{DS} = 60 \ V, V_C = 48 \ V, T_C = 25 \ V_D = 48 \ V, T_C = 25 \ V_D = 48 \ V, T_C = 25 \ V_D = 48 \ V, T_C = 25 \ V_D = 48 \ V, T_C = 25 \ V_D = 48 \ V, T_C = 25 \ V, V_D $	ParameterTest ConditionspracteristicsDrain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}, I_D = 250 \mu \text{A}$ Breakdown Voltage Temperature Coefficient $I_D = 250 \mu \text{A}, \text{Referenced tr}25^{\circ}\text{C}Zero Gate Voltage Drain CurrentV_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}Gate-Body Leakage Current, ForwardV_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}Gate-Body Leakage Current, ReverseV_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}Gate Threshold VoltageV_{DS} = V_{GS}, I_D = 250 \mu \text{A}Static Drain-Source On-ResistanceV_{GS} = 10 \text{ V}, I_D = 5.0 \text{ A}Forward TransconductanceV_{DS} = 25 \text{ V}, I_D = 5.0 \text{ A}$	ParameterTest ConditionsrracteristicsDrain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}, I_D = 250 \mu \text{A}$ Breakdown Voltage Temperature Coefficient $I_D = 250 \mu \text{A}, \text{Referenced to}$ 25°C Zero Gate Voltage Drain Current $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 48 \text{ V}, T_C = 125^{\circ}\text{C}$ Gate-Body Leakage Current, Forward $V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, ReverseVGate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{A}$ Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 5.0 \text{ A}$ Forward Transconductance $V_{DS} = 25 \text{ V}, I_D = 5.0 \text{ A}$	ParameterTest ConditionsMin.tracteristicsImage: Display state of the system of t	ParameterTest ConditionsMin.Typ.tracteristicsDrain-Source Breakdown Voltage $V_{GS} = 0 \ V, \ I_D = 250 \ \mu A$ 60 Breakdown Voltage Temperature $I_D = 250 \ \mu A$, Referenced to 0.06 Coefficient $25^{\circ}C$ 0.06 Zero Gate Voltage Drain Current $V_{DS} = 60 \ V, \ V_{GS} = 0 \ V$ Gate-Body Leakage Current, Forward $V_{GS} = 25 \ V, \ V_{DS} = 0 \ V$ Gate-Body Leakage Current, Reverse $V_{GS} = -25 \ V, \ V_{DS} = 0 \ V$ tracteristicsStatic Drain-Source On-Resistance $V_{GS} = 10 \ V, \ I_D = 5.0 \ A$ 2.0Forward Transconductance $V_{DS} = 25 \ V, \ I_D = 5.0 \ A$ 4.9	ParameterTest ConditionsMin.Typ.Max.tracteristicsDrain-Source Breakdown Voltage $V_{GS} = 0 V$, $I_D = 250 \mu A$ 60 Breakdown Voltage Temperature $I_D = 250 \mu A$, Referenced to 0.06 Zero Gate Voltage Drain Current $V_{DS} = 60 V$, $V_{GS} = 0 V$ 1 $V_{DS} = 48 V$, $T_C = 125^{\circ}C$ 10 $1000000000000000000000000000000000000$











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FQD13N06 — N-Channel QFET[®] MOSFET



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